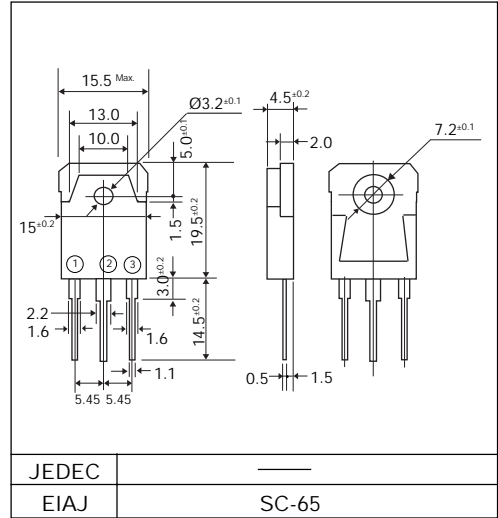


(200V to 400V / 15A)

FAST RECOVERY DIODE

■ Outline drawings, mm



■ Features

- High voltage by mesa design
- High reliability

- High voltage by mesa design
- High reliability

- Applications
 - High speed switching

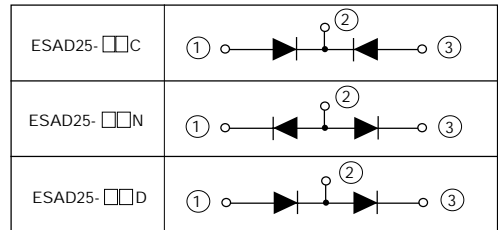
- High speed switching

■ Maximum ratings and characteristics

- Absolute maximum ratings

- Absolute maximum ratings

■ Connection diagram



Item	Symbol	Conditions	Rating		Unit
			-02	-04	
Repetitive peak reverse voltage	V_{RRM}		200	400	V
Non-repetitive peak reverse voltage	V_{RSM}		250	450	V
Average output current	I_o	Square wave, duty=1/2, $T_c=100^{\circ}C$	15*		A
Surge current	I_{FSM}	Sine wave 10ms	120		A
Operating junction temperature	T_j		-40 to +150		$^{\circ}C$
Storage temperature	T_{stg}		-40 to +150		$^{\circ}C$

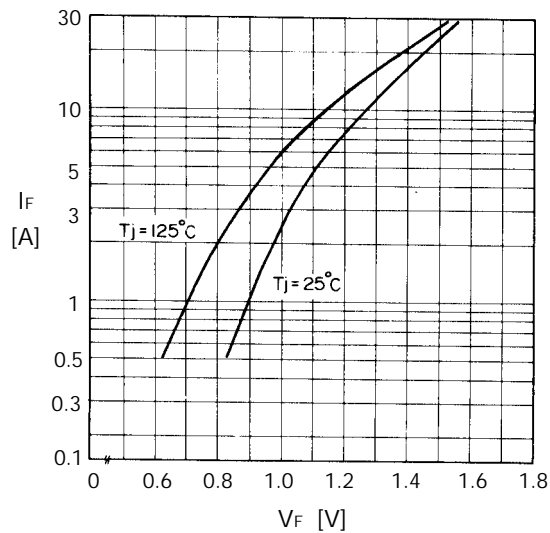
* Average forward current of center tap full wave connection

- Electrical characteristics (Ta=25°C Unless otherwise specified)

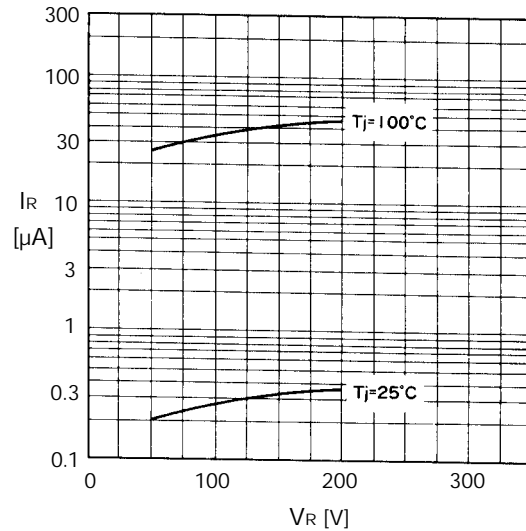
Item	Symbol	Conditions	Max.	Unit
Forward voltage drop	V_{FM}	$I_{FM}=8.0A$	1.3	V
Reverse current	I_{RRM}	$V_R=V_{RRM}$	0.1	mA
Reverse recovery time	t_{rr}	$I_F=0.1A, I_R=0.1A$	0.4	μs
Thermal resistance	$R_{th(j-c)}$	Junction to case	2.0*	$^{\circ}C/W$

Characteristics

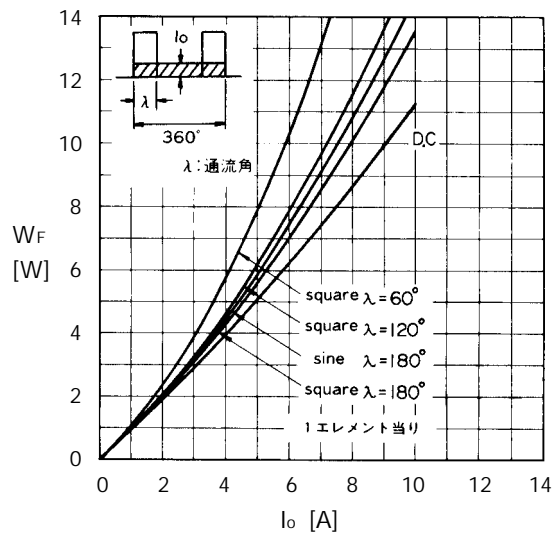
Forward characteristics



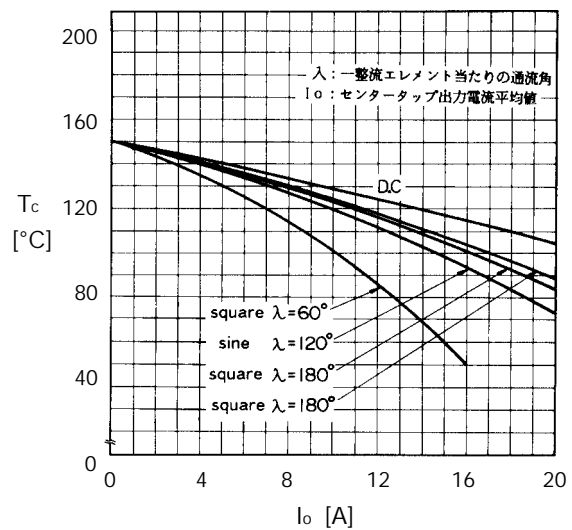
Reverse characteristics



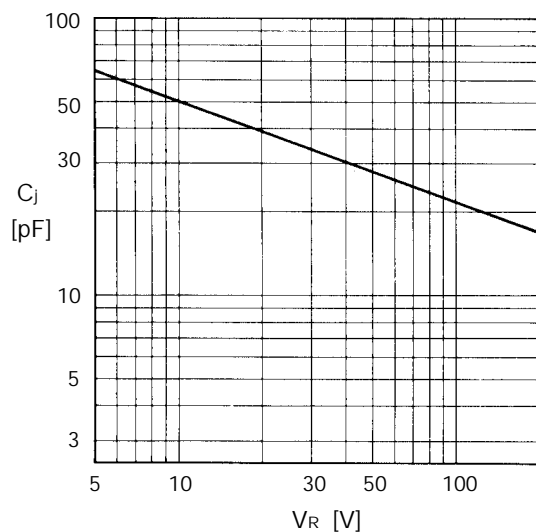
Forward power dissipation



Output current-case temperature



Junction capacitance characteristics



Surge capability

